



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Docket No.: FIS920030241US1

Huajie Chen, et al.

Serial No.: 10/689,506

Group Art Unit: Unassigned

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Examiner: Unassigned

For: **HIGH PERFORMANCE STRESS-ENHANCED MOSFETs USING Si:C AND SiGe EPITAXIAL SOURCE/DRAIN AND METHOD OF MANUFACTURE**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUBMISSION OF FORMAL DRAWINGS

Sir:

Submitted herewith, are five (5) sheets of formal drawings comprising figures 1-3 for the above-identified patent application. Please substitute the formal drawings for the drawings which were filed with the application.

Respectfully submitted,

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